

IN THE UNITED STATES PATENT & TRADEMARK OFFICE

JN RE APPLICATION OF:

Kwan Ju Koh

222

APPLICATION NO: 10/765,027

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FILED: January 26, 2004

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**FOR: METHODS OF  
MANUFACTURING MOSFET  
DEVICES**

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I hereby certify that this document is being transmitted to the USPTO or deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on June 25, 2009.

By: Judy Ryan  
Judy Ryan

REQUEST FOR A CERTIFICATE OF CORRECTION UNDER 37 CFR 1.322

ATTENTION: Certificate of Correction Branch  
COMMISSIONER FOR PATENTS  
OFFICE OF PATENT PUBLICATION  
P.O. BOX 1450  
ALEXANDRIA, VA 22313-1450  
FAX: (571) 273-8300

SIR:

Applicants respectfully request a Certificate of Correction in the above-referenced patent.

The facts are as follows:

Typographical errors appear in the above referenced patent as issued that resulted from errors by the U.S. Patent and Trademark Office. Applicants respectfully request a Certificate of Correction to correct the typographical errors. No new matter or new issues requiring further examination are introduced by the requested corrections.

Column 2, line 46 of the issued patent recites: "farming a first oxide layer". Applicant requests that the statement be corrected to state: "forming a first oxide layer".

Column 2, line 54 of the issued patent recites: "including the tightly doped drain". Applicant requests that the statement be corrected to state: "including the lightly doped drain".

Column 2, line 57 of the issued patent recites: "forming a second oxide layer aver an exposed portion". Applicant requests that the statement be corrected to state: "forming a second oxide layer over an exposed portion".

Column 2, line 62 of the issued patent recites: "first aid do layer". Applicants request that the statement be corrected to state: "first oxide layer".

Column 3, lines 24-25 of the issued patent recites: "etching to exposed substrate". Applicants request that the statement be corrected to state: "etching the exposed substrate".

Column 3, line 31 of the issued patent recites: "removing to first nitride layer". Applicants request that the statement be corrected to state: "removing the first nitride layer".

Column 3, line 32 of the issued patent recites: "to polysilicon layer". Applicants request that the statement be corrected to state: "the polysilicon layer".

**The corrections requested are as follows:**

Column 2, line 46 of the issued patent: change "farming a first oxide layer" to --forming a first oxide layer--.

Atty. Docket No. PIA31191/ANS/US  
Application No: 10/765,027

Column 2, line 54 of the issued patent: change "including the tightly doped drain" to --including the lightly doped drain--.

Column 2, line 57 of the issued patent: change "forming a second oxide layer over an exposed portion" to --forming a second oxide layer over an exposed portion--.

Column 2, line 62 of the issued patent: change "first aid do layer" to --first oxide layer--.

Column 3, lines 24-25 of the issued patent: change "etching to exposed substrate" to --etching the exposed substrate--.

Column 3, line 31 of the issued patent: change "removing to first nitride layer" to --removing the first nitride layer--.

Column 3, line 32 of the issued patent: change "to polysilicon layer" to --the polysilicon layer--.

Any additional information and/or assistance with this Request may be obtained from the undersigned practitioner.

Respectfully submitted,

/William K. Nelson/

William K. Nelson  
Reg. No. 63,501

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Reg. No. 34,600

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ADF:wkn:mah

**UNITED STATES PATENT AND TRADEMARK OFFICE  
CERTIFICATE OF CORRECTION**

Page 1 of 1

PATENT NO. : 7,192,837

APPLICATION NO.: 10/765,027

ISSUE DATE : March 20, 2007

INVENTOR(S) : Kwan Ju Koh

It is certified that an error appears or errors appear in the above-identified patent and that said Letters Patent is hereby corrected as shown below:

**IN THE CLAIMS**

Column 2, line 46 of the issued patent: change "farming a first oxide layer" to --forming a first oxide layer--.

Column 2, line 54 of the issued patent: change "including the tightly doped drain" to --including the lightly doped drain--.

Column 2, line 57 of the issued patent: change "second oxide layer aver an exposed portion" to --second oxide layer over an exposed portion--.

Column 2, line 62 of the issued patent: change "first aid do layer" to --first oxide layer--.

Column 3, lines 24-25 of the issued patent: change "etching to exposed substrate" to --etching the exposed substrate--.

Column 3, line 31 of the issued patent: change "removing to first nitride layer" to --removing the first nitride layer--.

Column 3, line 32 of the issued patent: change "to polysilicon layer" to --the polysilicon layer--.

**MAILING ADDRESS OF SENDER (Please do not use customer number below):**

The Law Offices of Andrew D. Fortney, Ph.D., P.C.  
401 W. Fallbrook Avenue, Suite 204  
Fresno, CA 93711

This collection of information is required by 37 CFR 1.322, 1.323, and 1.324. The information is required to obtain or retain a benefit by the public which is to file (and by the USPTO to process) an application. Confidentiality is governed by 35 U.S.C. 122 and 37 CFR 1.14. This collection is estimated to take 1.0 hour to complete, including gathering, preparing, and submitting the completed application form to the USPTO. Time will vary depending upon the individual case. Any comments on the amount of time you require to complete this form and/or suggestions for reducing this burden, should be sent to the Chief Information Officer, U.S. Patent and Trademark Office, U.S. Department of Commerce, P.O. Box 1450, Alexandria, VA 22313-1450. DO NOT SEND FEES OR COMPLETED FORMS TO THIS ADDRESS. SEND TO: Attention Certificate of Corrections Branch, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450.

*If you need assistance in completing the form, call 1-800-PTO-9199 and select option 2.*

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